

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

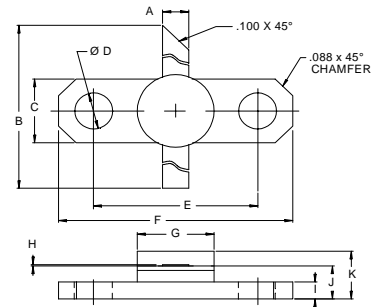
The **ASI MSC81035M** is a common base device, medium power Class C transistor for pulsed L-Band avionics, DME/TACAN Applications.

FEATURES:

- Input matching
- Emitter site Ballasted.
- $P_G = 10$ dB at 35 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CC}	55 V
P_{DISS}	150 W @ $T_C \leq 100$ °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.0 °C/W

PACKAGE STYLE .250 2L FLG (B)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			V
BV_{CER}	$I_C = 10$ mA $R_{BE} = 10$ Ω	65			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 50$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
P_G	$V_{CC} = 50$ V $P_{OUT} = 35$ W $f = 1025-1150$ MHz	10.7	11.2		dB
η_c	$P_{IN} = 3.0$ W	43	48		%